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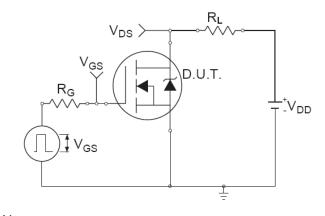
Features

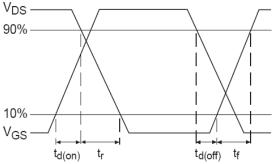
- V_{DSS} =320V/ V_{GSS} =±25V/ I_{D} =190A*** $R_{DS(ON)}$ =507m $\Omega(max.)$ @ V_{GS} =10V
- Low Dense Cell Design
- Reliable and Rugged
- Advanced trench process technology

Applications

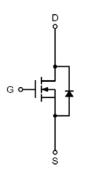
- Synchronous Rectification
- Power Management in Inverter System

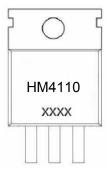
Switching Time Test Circuit and Waveforms





Pin Description





Marking and pin Assignment



TO-220-3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM4110	HM4110	TO-220-3L	-	-	-

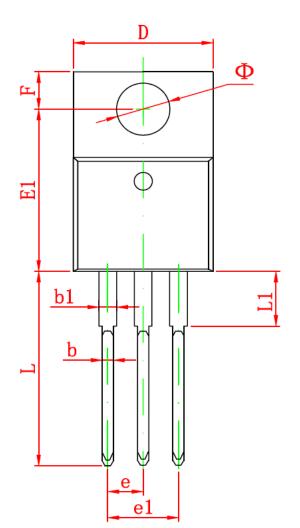
Electrical Characteristics of CP Test (TA=25°C unless otherwise noted)

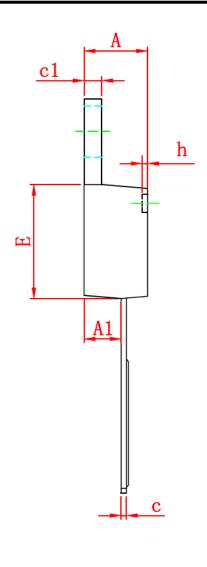
Symbol	Parameter	Test Conditions	Min.	Тур	Max.	Unit	
Static Characteristics							
BV_{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V,I _D =250uA	100			V	
I_{DSS}	Zero Gate Voltage Drain Current	V _{DS} =80V,V _{GS} =0V			1	uA	
		T _J =85°C	2		30		
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ,I _D =250uA	2	2.8	4	V	
I_{GSS}	Gate Leakage Current	V_{GS} =±25V, V_{DS} =0V			±100	nA	
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V, I _D =30A		4.5	5.5	mΩ	
V_{SD}	Diode Forward Voltage	I_{SD} =30A, V_{GS} =0V			1.3	V	
R_{G}	Gate Resistance	V _{GS} =0V, V _{DS} =0V, Frequency=1MHz		2		Ω	

Note: 1: Pulse test; pulse width ≤ 300 ns, duty cycle $\leq 2\%$.

^{2:} Guaranteed by design, not subject to production testing.

TO-220-3L PACKAGE OUTLINE DIMENSIONS





Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Syllibol	Min	Max	Min	Max	
Α	4.470	4.670	0.176	0.184	
A1	2.520	2.820	0.099	0.111	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.310	0.530	0.012	0.021	
c1	1.170	1.370	0.046	0.054	
D	10.010	10.310	0.394	0.406	
E	8.500	8.900	0.335	0.350	
E1	12.060	12.460	0.475	0.491	
е	2.540) TYP	0.100 TYP		
e1	4.980	5.180	0.196	0.204	
F	2.590	2.890	0.102	0.114	
h	0.000	0.300	0.000	0.012	
L	13.400	13.800	0.528	0.543	
L1	3.560	3.960	0.140	0.156	
Ф	3.735	3.935	0.147	0.155	

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100V_{DS}/±25V_{GS}/170A(I_D) N-Channel Enha ncement Mode MOSFET

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